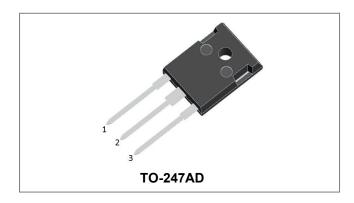


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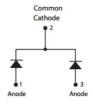
MBR4060WT SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=120°C, rectangular wave form	20(Per Leg) 40(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	400	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 20A, Pulse, T _J = 25 °C	0.65	0.75	V
(per leg) *	V _{F2}	@ 20A, Pulse, T _J = 125 °C	0.62	0.65	V
Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_R \text{ Pulse}$ $T_J = 25 ^{\circ}\text{C}$	0.1	1.0	mA
	I _{R2}	$@V_R = \text{rated } V_R$, Pulse $T_J = 125 ^{\circ}\text{C}$	28	75	mA
Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	400	900	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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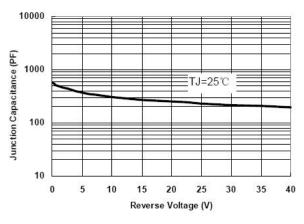




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.5	°C/W
Typical Thermal Resistance Case to Heat Sink	R ₀ CS	Mounting surface, smooth and greased(only for TO-220)	0.50	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves



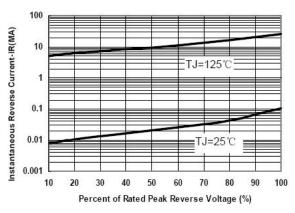


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

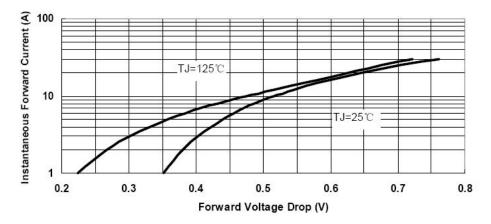


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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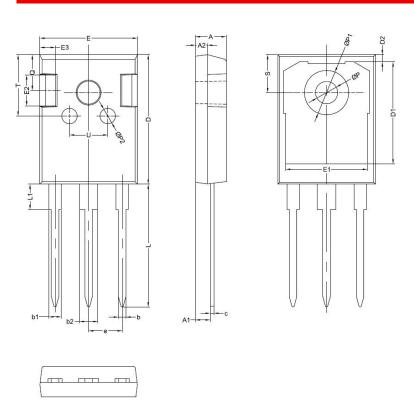


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Mechanical Dimensions TO-247AD



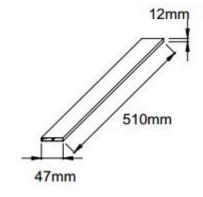
2,412.	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
D2 E	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
		5.80			
Q S T	6.05	6.15	6.25		
T		10.00			
U		6.20			

Ordering Information:

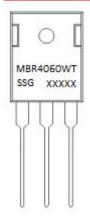
Device	Package	Shipping	
MBR4060WT	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 MBR
 = Device Type

 40
 = Forward Current (40A)

 60
 = Reverse Voltage (60V)

 WT
 = Configuration

 SSG
 = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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MBR4060WT



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